



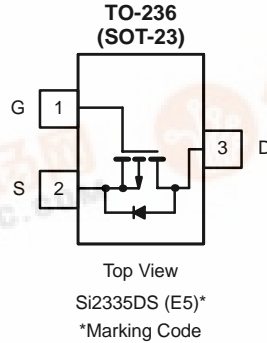
New Product

Si2335DS
Vishay Siliconix

P-Channel 12-V (D-S) MOSFET

TrenchFET[®]
Power MOSFETs
1.8-V Rated

PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)
-12	0.051 @ V _{GS} = -4.5 V	-4.0
	0.070 @ V _{GS} = -2.5 V	-3.5
	0.106 @ V _{GS} = -1.8 V	-3.0



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)				
Parameter	Symbol	5 sec	Steady State	Unit
Drain-Source Voltage	V _{DS}	-12		V
Gate-Source Voltage	V _{GS}	±8		
Continuous Drain Current (T _J = 150°C) ^{a, b}	T _A = 25°C	-4.0	-3.2	A
	T _A = 70°C	-3.3	-2.6	
Pulsed Drain Current	I _{DM}	-15		
Continuous Source Current (Diode Conduction) ^{a, b}	I _S	-1.6		
Maximum Power Dissipation ^{a, b}	T _A = 25°C	1.25	0.75	W
	T _A = 70°C	0.8	0.48	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 5 sec	75	100	°C/W
	Steady State	120	166	
Maximum Junction-to-Foot (Drain)	Steady State	40	50	

Notes:
 a. Surface Mounted on 1" x 1" FR4 Board.
 b. Pulse width limited by maximum junction temperature.

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SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = -10 μA	-12			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.45			
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -9.6 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -9.6 V, V _{GS} = 0 V, T _J = 55 °C			-10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ -5 V, V _{GS} = -4.5 V	-15			A
		V _{DS} ≤ -5 V, V _{GS} = -2.5 V	-6			
Drain-Source On-Resistance ^a	r _{DS(on)}	V _{GS} = -4.5 V, I _D = -4.0 A		0.042	0.051	Ω
		V _{GS} = -2.5 V, I _D = -3.5 A		0.058	0.070	
		V _{GS} = -1.8 V, I _D = -2.0 A		0.082	0.106	
Forward Transconductance ^a	g _{fs}	V _{DS} = -5 V, I _D = -4.0 A		7		S
Diode Forward Voltage	V _{SD}	I _S = -1.6 A, V _{GS} = 0 V			-1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = -6 V, V _{GS} = -4.5 V I _D ≅ -4.0 A		9	15	nC
Gate-Source Charge	Q _{gs}			1.9		
Gate-Drain Charge	Q _{gd}			1.5		
Input Capacitance	C _{iss}	V _{DS} = -6 V, V _{GS} = 0, f = 1 MHz		1225		pF
Output Capacitance	C _{oss}			260		
Reverse Transfer Capacitance	C _{rss}			130		
Switching^c						
Turn-On Time	t _{d(on)}	V _{DD} = -6 V, R _L = 6 Ω I _D ≅ -1.0 A, V _{GEN} = -4.5 V R _G = 6 Ω		13.0	20	ns
	t _r			15	25	
Turn-Off Time	t _{d(off)}			50	70	
	t _f			19	35	

Notes

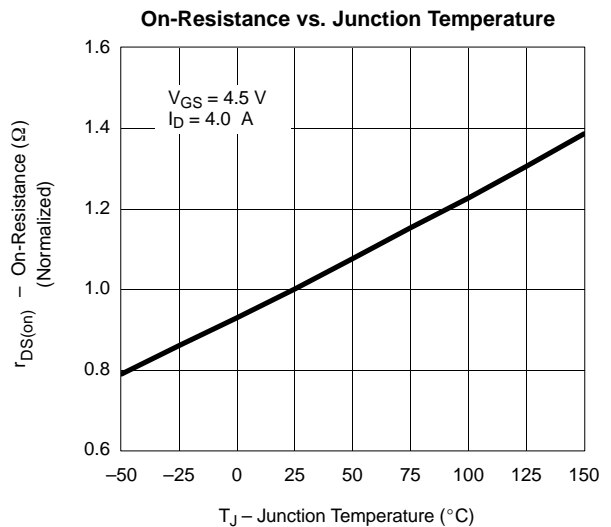
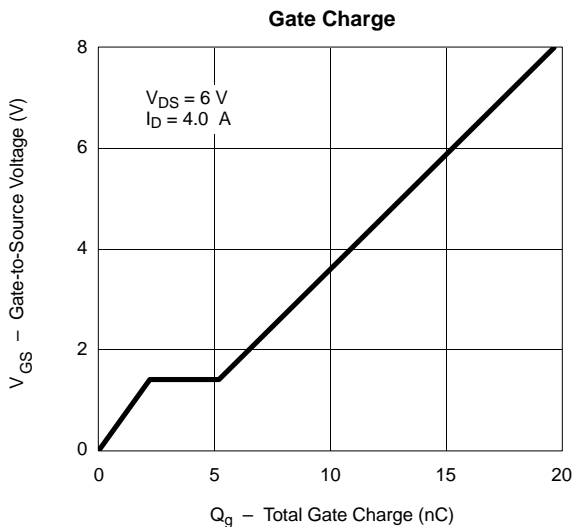
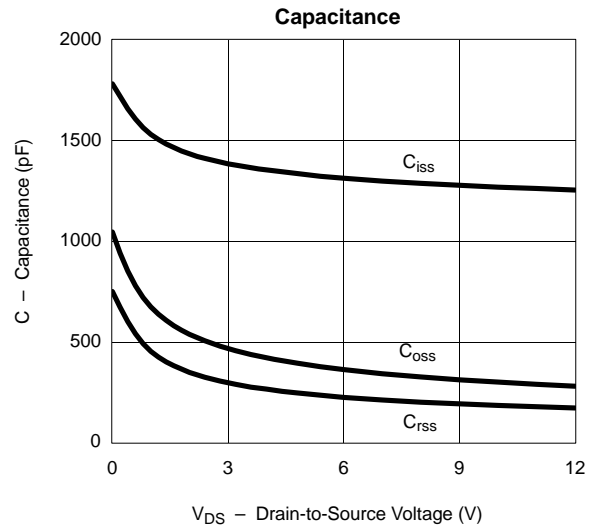
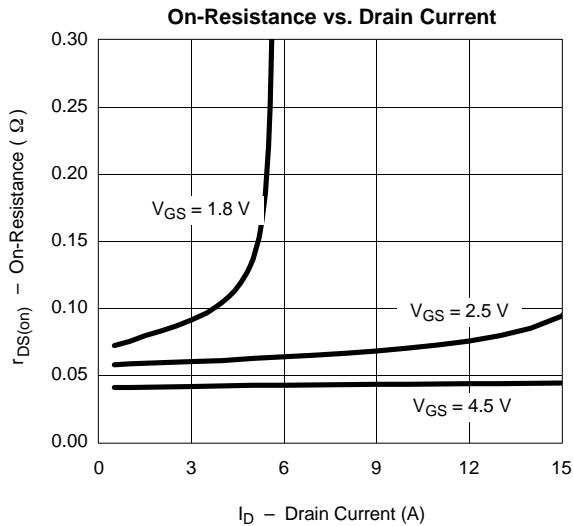
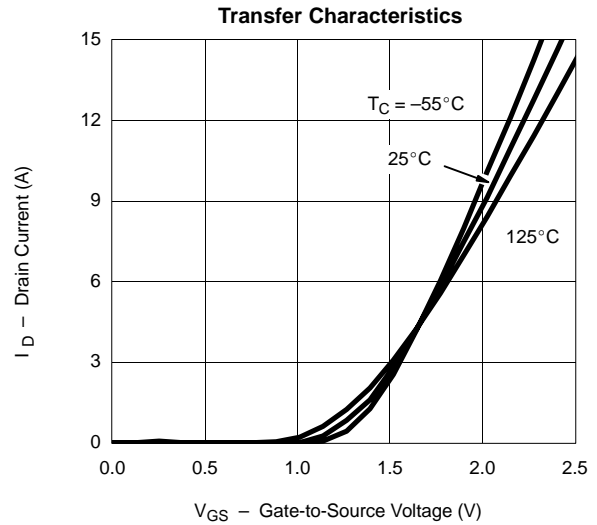
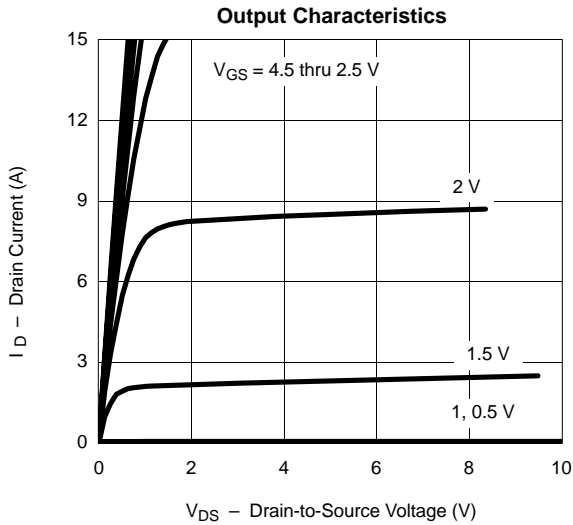
- a. Pulse test: PW ≤ 300 μs duty cycle ≤ 2%.
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.



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TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



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